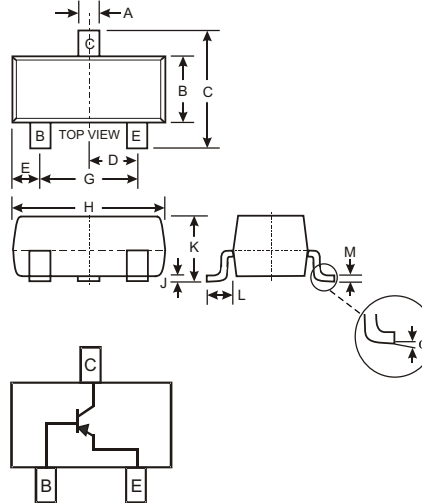


### Features

- Epitaxial Planar Die Construction
- Complementary NPN Type Available (MMBT3904)
- Ideal for Medium Power Amplification and Switching
- Also Available in Lead Free Version

### Mechanical Data

- Case: SOT-23, Molded Plastic
- Case material - UL Flammability Rating Classification 94V-0
- Moisture sensitivity: Level 1 per J-STD-020A
- Terminals: Solderable per MIL-STD-202, Method 208
- Also Available in Lead Free Plating (Matte Tin Finish). Please see Ordering Information, Note 4, on Page 2
- Terminal Connections: See Diagram
- Marking (See Page 2): K3N
- Ordering & Date Code Information: See Page 2
- Weight: 0.008 grams (approx.)



SOT-23		
Dim	Min	Max
A	0.37	0.51
B	1.20	1.40
C	2.30	2.50
D	0.89	1.03
E	0.45	0.60
G	1.78	2.05
H	2.80	3.00
J	0.013	0.10
K	0.903	1.10
L	0.45	0.61
M	0.085	0.180
$\alpha$	0°	8°
All Dimensions in mm		

### Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	MMBT3906	Unit
Collector-Base Voltage	$V_{CB0}$	-40	V
Collector-Emitter Voltage	$V_{CE0}$	-40	V
Emitter-Base Voltage	$V_{EB0}$	-5.0	V
Collector Current - Continuous (Note 1)	$I_C$	-200	mA
Power Dissipation (Note 1)	$P_d$	300	mW
Thermal Resistance, Junction to Ambient (Note 1)	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Operating and Storage and Temperature Range	$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$

Notes: 1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.

## Electrical Characteristics @ T<sub>A</sub> = 25°C unless otherwise specified

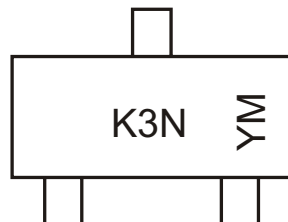
Characteristic	Symbol	Min	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 2)</b>					
Collector-Base Breakdown Voltage	V <sub>(BR)CBO</sub>	-40	—	V	I <sub>C</sub> = -10μA, I <sub>E</sub> = 0
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	-40	—	V	I <sub>C</sub> = -1.0mA, I <sub>B</sub> = 0
Emitter-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	-5.0	—	V	I <sub>E</sub> = -10μA, I <sub>C</sub> = 0
Collector Cutoff Current	I <sub>CEX</sub>	—	-50	nA	V <sub>CE</sub> = -30V, V <sub>EB(OFF)</sub> = -3.0V
	I <sub>CBO</sub>	—	-50	nA	V <sub>CB</sub> = -30V, I <sub>E</sub> = 0
Base Cutoff Current	I <sub>BL</sub>	—	-50	nA	V <sub>CE</sub> = -30V, V <sub>EB(OFF)</sub> = -3.0V
<b>ON CHARACTERISTICS (Note 2)</b>					
DC Current Gain	h <sub>FE</sub>	60	—	—	I <sub>C</sub> = -100μA, V <sub>CE</sub> = -1.0V I <sub>C</sub> = -1.0mA, V <sub>CE</sub> = -1.0V I <sub>C</sub> = -10mA, V <sub>CE</sub> = -1.0V I <sub>C</sub> = -50mA, V <sub>CE</sub> = -1.0V I <sub>C</sub> = -100mA, V <sub>CE</sub> = -1.0V
		80	—		
		100	300		
		60	—		
		30	—		
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	—	-0.25 -0.40	V	I <sub>C</sub> = -10mA, I <sub>B</sub> = -1.0mA I <sub>C</sub> = -50mA, I <sub>B</sub> = -5.0mA
Base- Emitter Saturation Voltage	V <sub>BE(SAT)</sub>	-0.65 —	-0.85 -0.95	V	I <sub>C</sub> = -10mA, I <sub>B</sub> = -1.0mA I <sub>C</sub> = -50mA, I <sub>B</sub> = -5.0mA
<b>SMALL SIGNAL CHARACTERISTICS</b>					
Output Capacitance	C <sub>obo</sub>	—	4.5	pF	V <sub>CB</sub> = -5.0V, f = 1.0MHz, I <sub>E</sub> = 0
Input Capacitance	C <sub>ibo</sub>	—	10	pF	V <sub>EB</sub> = -0.5V, f = 1.0MHz, I <sub>C</sub> = 0
Input Impedance	h <sub>ie</sub>	2.0	12	kΩ	V <sub>CE</sub> = 10V, I <sub>C</sub> = 1.0mA, f = 1.0kHz
Voltage Feedback Ratio	h <sub>re</sub>	0.1	10	x 10 <sup>-4</sup>	
Small Signal Current Gain	h <sub>fe</sub>	100	400	—	
Output Admittance	h <sub>oe</sub>	3.0	60	μS	
Current Gain-Bandwidth Product	f <sub>T</sub>	250	—	MHz	
Noise Figure	NF	—	4.0	dB	V <sub>CE</sub> = -5.0V, I <sub>C</sub> = -100μA, R <sub>S</sub> = 1.0kΩ, f = 1.0kHz
<b>SWITCHING CHARACTERISTICS</b>					
Delay Time	t <sub>d</sub>	—	35	ns	V <sub>CC</sub> = -3.0V, I <sub>C</sub> = -10mA, V <sub>BE(off)</sub> = 0.5V, I <sub>B1</sub> = -1.0mA
Rise Time	t <sub>r</sub>	—	35	ns	
Storage Time	t <sub>s</sub>	—	225	ns	V <sub>CC</sub> = -3.0V, I <sub>C</sub> = -10mA, I <sub>B1</sub> = I <sub>B2</sub> = -1.0mA
Fall Time	t <sub>f</sub>	—	75	ns	

## Ordering Information (Note 3)

Device	Packaging	Shipping
MMBT3906 -7	SOT-23	3000/Tape & Reel

- Notes:
2. Short duration test pulse used to minimize self-heating effect.
  3. For Packaging Details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.
  4. For Lead Free version (with Lead Free terminal finish) part number, please add "-F" suffix to part number above.  
Example: MMBT3906-7-F.

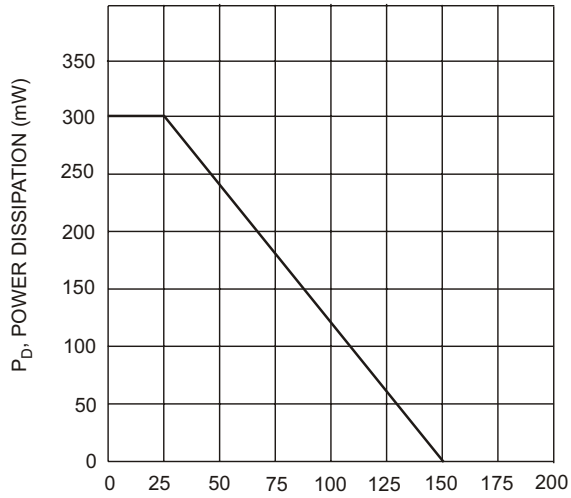
## Marking Information



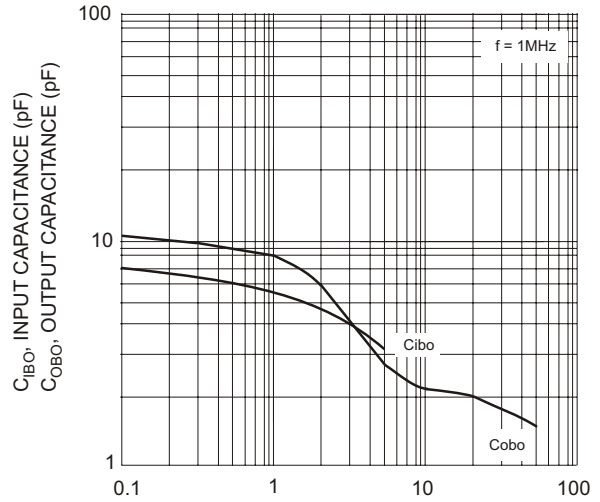
K3N = Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year ex: N = 2002  
 M = Month ex: 9 = September

Date Code Key

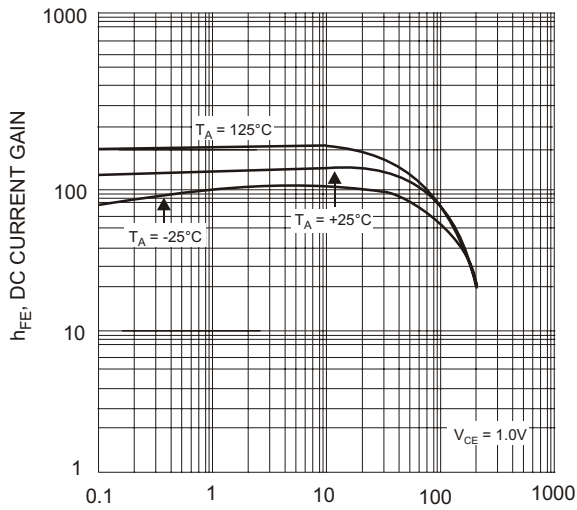
Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009
Code	J	K	L	M	N	P	R	S	T	U	V	W
Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D



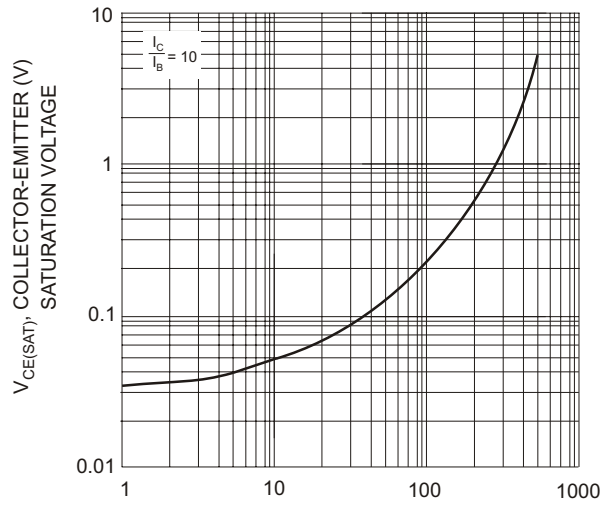
T<sub>A</sub>, AMBIENT TEMPERATURE (°C)  
Fig. 1, Max Power Dissipation vs Ambient Temperature



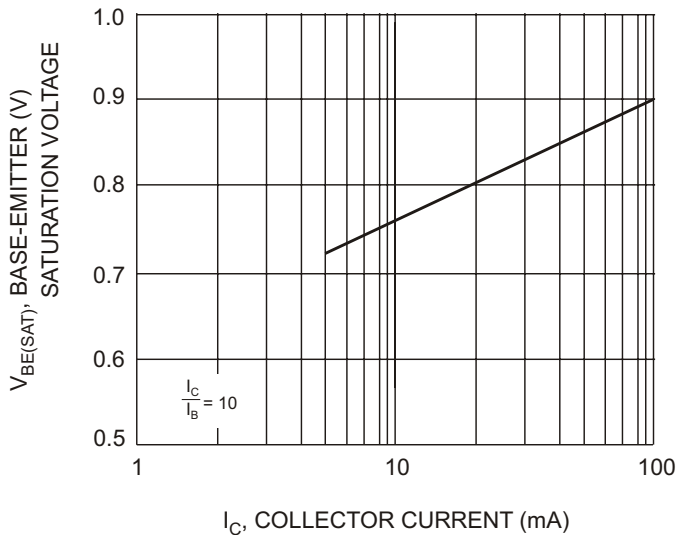
V<sub>CB</sub>, COLLECTOR-BASE VOLTAGE (V)  
Fig. 2, Input and Output Capacitance vs. Collector-Base Voltage



I<sub>C</sub>, COLLECTOR CURRENT (mA)  
Fig. 3, Typical DC Current Gain vs Collector Current



I<sub>C</sub>, COLLECTOR CURRENT (mA)  
Fig. 4, Typical Collector-Emitter Saturation Voltage vs. Collector Current



I<sub>C</sub>, COLLECTOR CURRENT (mA)  
Fig. 5, Typical Base-Emitter Saturation Voltage vs. Collector Current